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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the application of: )  
 )  
Christian Schott et al. )  
 )  
Title: MAGNETIC FIELD SENSOR WITH )  
A HALL ELEMENT )  
 )  
Serial No.: National Stage Entry of )  
Int'l Appln. No: PCT/CH02/00497 )  
Int'l Filing Date: September 10, 2002 )  
 )  
Filed On: Simultaneously herewith ) (Our Docket No: 6305-0010WOUS)

Hartford, Connecticut – March 10, 2005

Mail Stop PCT  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

SIR:

Enclosed is Form PTO/SB/08A and 08B listing documents believed to be relevant to the above-referenced patent application. It is respectfully requested that the Examiner consider the listed documents and an initialed copy of the form be returned to the undersigned.

The filing of this Information Disclosure Statement shall not be construed as a representation that a search has been made (37 CFR 1.97(g)), an admission that the information cited is, or is considered to be, material to patentability, or that no other material information exists.

The listed documents are:

<u>U.S. Patent No.</u>	<u>Entitled</u>	<u>Dated</u>
4, 037150	METHOD OF AND APPARATUS FOR ELIMINATING THE EFFECT OF NON-EQUIPOTENTIALITY VOLTAGE ON THE HALL VOLTAGE	07-19-1977
5,057,890*	HALL ELEMENT	10-15-1991
5,572,058	HALL EFFECT DEVICE FORMED IN AN EPITAXIAL LAYER OF SILICON FOR SENSING MAGNETIC FIELDS PARALLEL TO THE EPITAXIAL LAYER	11-05-1996

\*ENGLISH EQUIVALENT TO EP 0 362 493 A

<u>Foreign Patent No</u>	<u>Country</u>	<u>Dated</u>
EP 0 362 493*	Europe	07-11-1989

\* U.S. EQUIVALENT IDENTIFIED ABOVE.

A copy of the cited foreign reference is enclosed along with the equivalent U.S. patent for the one German language EP patent.

NON-PATENT LITERATURE DOCUMENTS:

FALK, U: "A symmetrical vertical Hall-effect device", SENSORS AND ACTUATORS A (PHYSICAL), Bd. A22, Nr. 1-3, MARCH 1990 (1990-03), pages 751-753, XP000358526 ISSN: 0924-4247

ROUMENIN, C S : "Parallel-field Hall microsensors: an overview", SENSORS AND ACTUATORS A (PHYSICAL), Bd. A30, No. 1-2 January 1992 (1992-01), pages 77-87, XP000277696 ISSN: 0924-4247

SCHURIG, E et al.: "CMOS Integrated vertical Hall sensor with low offset:", PROCEEDINGS EUROSensors XVI, 16TH EUROPEAN CONFERENCE ON SOLID-STATE TRANSDUCERS, Prague, Czech Republic, 15.-18. September 2002, pages 868-871, XP002241233

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NON-PATENT LITERATURE DOCUMENTS (CONT.):

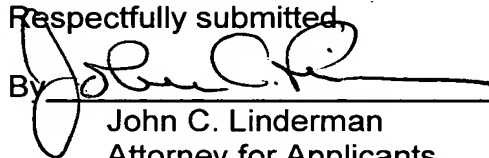
STEINER, R et al. "Double-Hall sensor with self-compensated offset",  
INTERNATIONAL ELECTRON DEVICES MEETING, IEDM 97, Washington,  
D.C. USA, 7.-10. Dezember pages 911-914, XP000855940 ISBN: 0-7803-  
4100-7

SCHURIG, E et al: "A vertical Hall device in CMOS integrated high-voltage  
technology", SENSORS AND ACTUATORS A (PHYSICAL), 97-98 (2002) 47-  
53

If any fees are due, Account No. 13-0235 maintained by Applicant's  
attorney may be charged.

Respectfully submitted,

By

  
John C. Linderman  
Attorney for Applicants  
Registration No. 24, 420

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Attachment SB/08A&B and 1 foreign reference and 5 non-patent references.

Approved for use through 07/31/2006. OMB 0651-0031

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Substitute for form 1449A/PTO

**Complete if Known**

**(Use as many sheets as necessary)**

Sheet

1

Q

2

Application Number

Filing Date

**First Named Inventor**

Schott et al.

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**Art Unit**

Examiner Name

Attorney Docket Number

6305-0010WOUS

[illegible]

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup> *Number <sup>4</sup> *Kind Code <sup>5</sup> (if known)				
		EP 0 362 493 A1*	07-11-89	Landis & Gyr Be	*U.S. EQUIVALNT	✓
		* US 5057890				

**Examiner  
Signature**

Date \_\_\_\_\_

**Date Considered**

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional). 2 See Kinds Codes of USPTO Patent Documents at [www.uspto.gov](http://www.uspto.gov) or MPEP 901.04. 3 Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). 4 For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. 5 Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. 6 Applicant is to place a check mark here if English language Translation is attached.

This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. **DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.**

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Substitute for form 1449B/PTO		<b>Complete if Known</b>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use as many sheets as necessary)		Application Number	
		Filing Date	
		First Named Inventor	Schott et al.
		Art Unit	
		Examiner Name	
Sheet 2 of 2	Attorney Docket Number	6305-0010WOUS	

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
		FALK U: "A symmetrical vertical Hall-effect device", SENSORS AND ACTUATORS A (PHYSICAL), Bd. A22, Nr. 1-3, MARCH 1990 (1990-03), pages 751-753, XP000358526 ISSN: 0924-4247	
		ROUMENIN C S : "Parallel-field Hall microsensors: an overview", SENSORS AND ACTUATORS A (PHYSICAL), Bd. A30, No. 1-2 January 1992 (1992-01), pages 77-87, XP000277696 ISSN: 0924-4247	
		SCHURIG E et al.: "CMOS Integrated vertical Hall sensor with low offset.", PROCEEDINGS EUROSENSORS XVI, 16TH EUROPEAN CONFERENCE ON SOLID-STATE TRANSDUCERS, Prague, Czech Republic, 15.-18. September 2002, pages 868-871, XP002241233	
		STEINER R et al. "Double-Hall sensor with self-compensated offset", INTERNATIONAL ELECTRON DEVICES MEETING, IEDM 97, Washington, D.C. USA, 7.-10. Dezember pages 911-914, XP000855940 ISBN: 0-7803-4100-7	
		SCHURIG E et al: "A vertical Hall device in CMOS integrated high-voltage technology", SENSORS AND ACTUATORS A (PHYSICAL), 97-98 (2002) 47-53	

Examiner Signature		Date Considered	
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Applicant's unique citation designation number (optional). <sup>2</sup> Applicant is to place a check mark here if English language Translation is attached.

This collection of information is required by 37 CFR 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 120 minutes to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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